

Clean Version of Amended Paragraph

P. 23, lines 10-20

AR The oxide etch characteristics of the multilayer regime were further investigated to provide identifying distinctions of this regime. There is shown in Fig. 7A a plot of oxide etch rate as a function of the partial pressure of water vapor, for a wafer temperature of 40° C, a total flow rate of 500 sccm, a total pressure of 250 T, and an HF vapor pressure of 7 T. These measurements were made on thermal oxide samples of about 5500 Å in thickness that were etched for several minutes while the thickness were measured using ellipsometry. The change in thickness per minute (etch rates) were computed from this data. From the plot it is seen that the multilayer regime is characterized by an oxide etch rate that is substantially linearly proportional to water vapor partial pressure.

Clean Version of Amended Paragraph

P. 16, lines 15-19

Al Fig. 2D depicts the final operational regime, in which the vapor process parameters result in a condition whereby vapor-phase reactants 50 form a sub-monolayer 62 on the surface of an oxide layer 54 to be etched on a silicon wafer 56. The sub-monolayer regime can be generally defined as one in which no more than about 95% of a monolayer exists.